

# N- and P-Channel 30-V (D-S) MOSFET

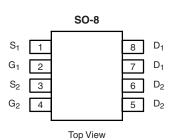
PRODUCT SUMMARY							
	V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)				
N-Channel	30	0.036 at V <sub>GS</sub> = 10 V	5.9				
		0.053 at V <sub>GS</sub> = 4.5 V	4.9				
P-Channel	- 30	0.053 at V <sub>GS</sub> = - 10 V	- 4.9				
	- 30	0.090 at V <sub>GS</sub> = - 4.5 V	- 3.7				

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC

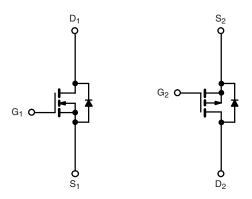


FREE



Ordering Information: Si4539ADY-T1-E3 (Lead (Pb)-free)

Si4539ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted								
Parameter			N-Channel		P-Channel			
		Symbol	10 s	Steady State	10 s	Steady State	Unit	
Drain-Source Voltage		$V_{DS}$	30		- 30		V	
Gate-Source Voltage		$V_{GS}$	± 20		± 20			
0 11	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	5.9	4.4	- 4.9	- 3.7		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		4.7	3.6	- 3.9	- 2.9	•	
Pulsed Drain Current		I <sub>DM</sub>	30				Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.7	0.9	- 1.7	- 0.9		
	T <sub>A</sub> = 25 °C	В	2.0	1.1	2	1.1	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	P <sub>D</sub>	1.3	0.7	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS									
Parameter			N-Ch	annel	P-Channel				
		Symbol	Тур.	Max.	Тур.	Max.	Unit		
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	50	62.5	52	62.5			
	Steady State	' 'thJA	90	110	90	110	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	32	40	32	40			

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	1.0			V		
	V GS(th)	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	P-Ch	- 1.0					
Cata Dadi Laskana		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	N-Ch			± 100	^		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	P-Ch			± 100	nA		
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	N-Ch			1			
		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V	P-Ch			- 1	μΑ		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	N-Ch			5			
		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	P-Ch			- 5			
		$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	N-Ch	30			А		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	P-Ch	- 30					
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.9 A	N-Ch		0.032 0.036				
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4.9 A	P-Ch		0.043	0.053			
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4.9 A	N-Ch		0.042	0.053	Ω		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.7 A	P-Ch		0.075	0.090			
	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.9 A	N-Ch		15				
Forward Transconductance <sup>a</sup>		V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 4.9 A	P-Ch		9		S		
	.,	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V	N-Ch		0.80	1.2	v		
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 1.7 A, V <sub>GS</sub> = 0 V	P-Ch		- 0.80	- 1.2			
Dynamic <sup>b</sup>									
Total Gate Charge	Qg	N Observat	N-Ch		13	20			
Total date onlinge	<b>u</b> g	N-Channel $V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5.9 \text{ A}$	P-Ch		15	25	nC		
Gate-Source Charge	$Q_{gs}$ $Q_{gd}$ $R_g$	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, 1 <sub>D</sub> = 0.0 N	N-Ch		2.3				
		P-Channel	P-Ch		4				
Gate-Drain Charge		$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -4.9 \text{ A}$	N-Ch P-Ch		2 2.0				
			N-Ch	0.5	2.0	2.2			
Gate Resistance			P-Ch	5		12.6			
	<sup>†</sup> d(on)		N-Ch		6	12			
Turn-On Delay Time		N-Channel	P-Ch		7	15			
Rise Time	+	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$	N-Ch		14	25			
	t <sub>r</sub>	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$	P-Ch		10	20			
Turn-Off Delay Time Fall Time	t <sub>d(off)</sub>	P-Channel	N-Ch		30	60	no		
	G(OII)	$V_{DD} = -15 \text{ V}, R_{L} = 15 \Omega$	P-Ch		40	80	ns		
	t <sub>f</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$	N-Ch		5	10			
	,	1 1 7 0 11/14 100 6/15	P-Ch		20	40			
Source-Drain	T I	I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs	N-Ch		30	60			
Reverse Recovery Time		I <sub>F</sub> = - 1.7 A, dI/dt = 100 A/μs	P-Ch		30	60			

#### Notes:

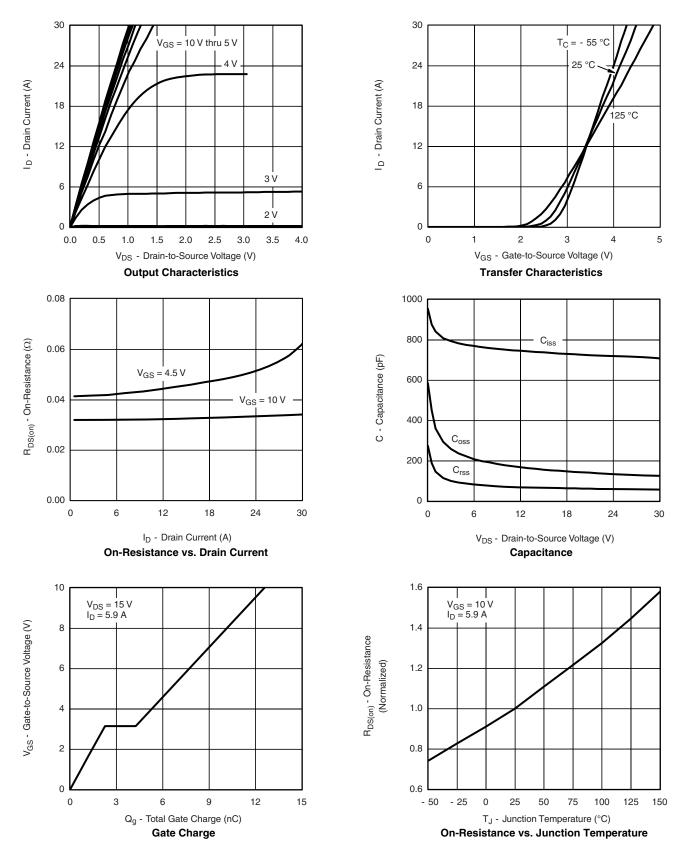
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

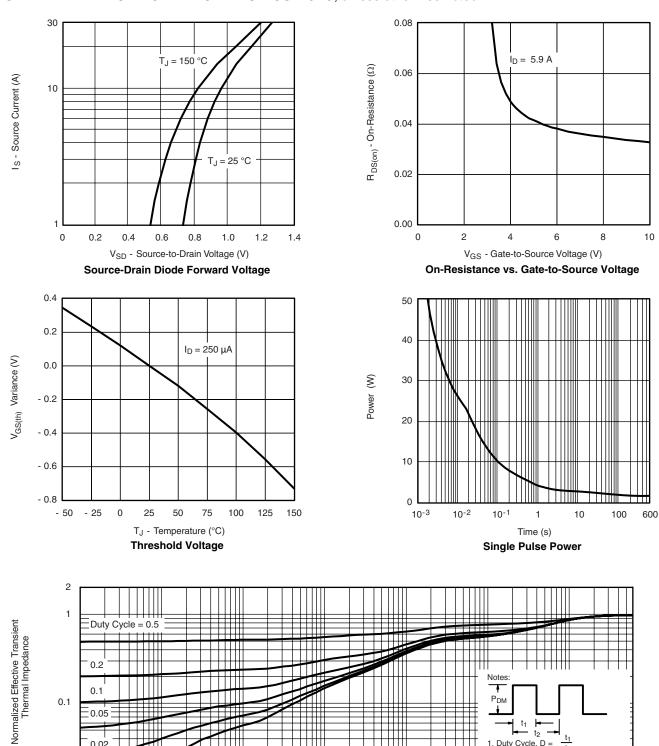


### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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#### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient

10-1

0.02

0.01 10-4 Single Pulse

10-2

10-3

600

1. Duty Cycle, D =

4. Surface Mounted

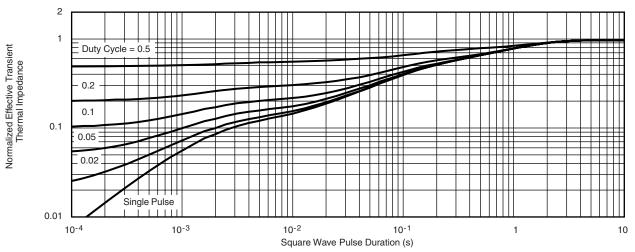
10

2. Per Unit Base = R<sub>thJA</sub> = 90 °C/W  $3.\,T_{JM}\, \cdot T_{A} = P_{DM}Z_{thJA}{}^{(t)}$ 

100

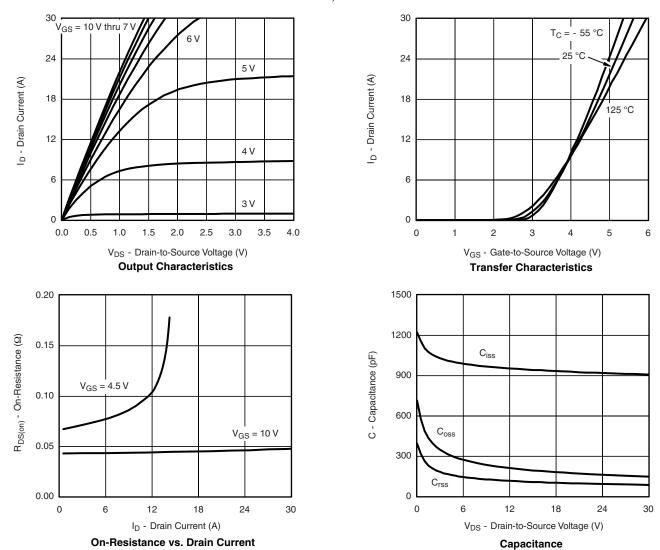


#### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

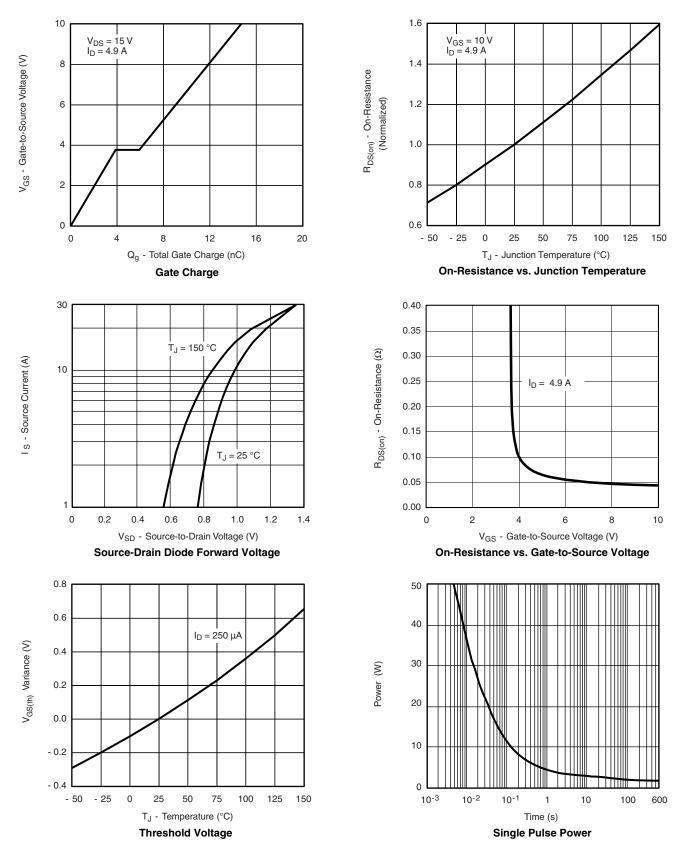
#### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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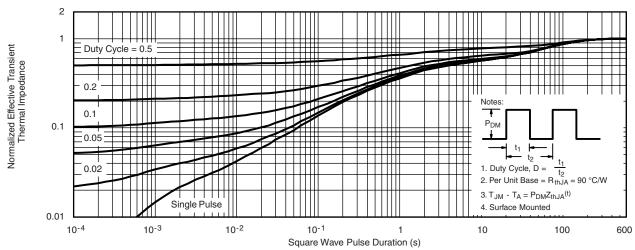


#### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

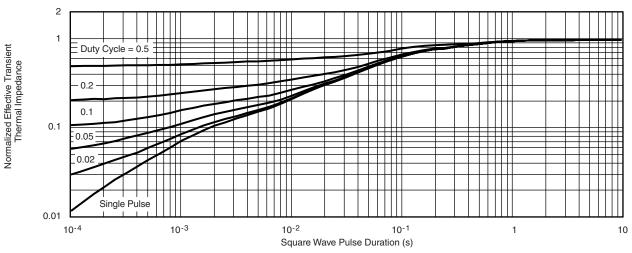




#### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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